BD180G

Plastic Medium-Power Silicon PNP Transistor

This device is designed for use in 5.0 to 10 Watt audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- BD180 is complementary with BD179
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	1.0	Adc
Base Current	Ι _Β	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	30 240	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

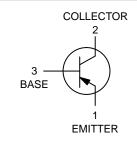
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.16	°C/W	



ON Semiconductor®

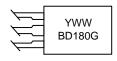
http://onsemi.com

3.0 AMPERES POWER TRANSISTORS PNP SILICON 80 VOLTS, 30 WATTS





MARKING DIAGRAM



Y = Year

WW = Work Week

BD180 = Device Code

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BD180G	TO-225 (Pb-Free)	500 Units/Box

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 0.1 Adc, I _B = 0)	V _{(BR)CEO}	80	_	Vdc
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	I _{CBO}	-	1.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	mAdc
DC Current Gain (I _C = 0.15 A, V _{CE} = 2.0 V) (I _C = 1.0 A, V _{CE} = 2.0 V)	h _{FE}	40 15	250 -	-
Collector–Emitter Saturation Voltage (Note 1) (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{CE(sat)}	-	0.8	Vdc
Base-Emitter On Voltage (Note 1) (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	1.3	Vdc
Current–Gain – Bandwidth Product ($I_C = 250 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	f _T	3.0	-	MHz

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

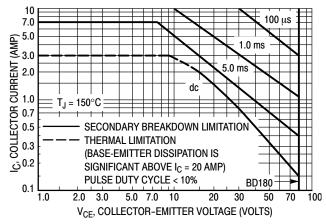


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power–temperature derating must be observed for both steady state and pulse power conditions.

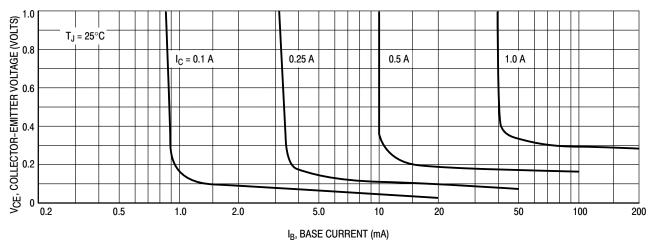
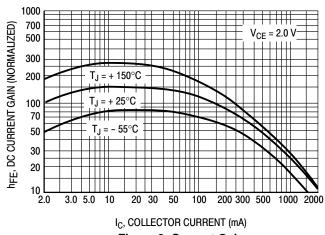


Figure 2. Collector Saturation Region

BD180G



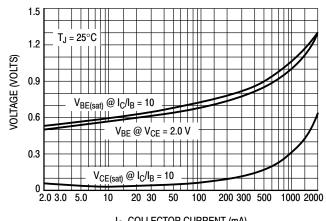


Figure 3. Current Gain

I_C, COLLECTOR CURRENT (mA) **Figure 4. "On" Voltages**

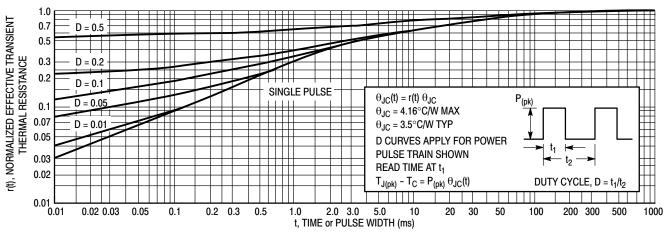
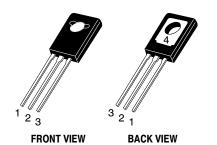


Figure 5. Thermal Response

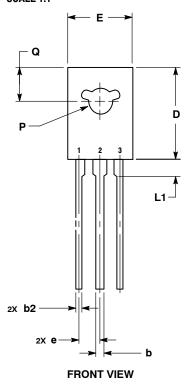
MECHANICAL CASE OUTLINE

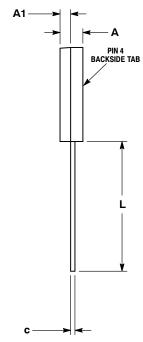


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1



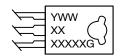


SIDE VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.40	3.00		
A1	1.00	1.50		
b	0.60	0.90		
b2	0.51	0.88		
С	0.39	0.63		
D	10.60	11.10		
E	7.40	7.80		
е	2.04	2.54		
L	14.50	16.63		
L1	1.27	2.54		
P	2.90	3.30		
Q	3.80 4.20			

GENERIC MARKING DIAGRAM*



= Year ww = Work Week XXXXX = Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

2., 4. DRAIN 3. GATE

= Pb-Free Package

	EMITTER COLLECTOR BASE	2., 4.	CATHODE ANODE GATE	STYLE 3: PIN 1. 2., 4. 3.	COLLECTOR	,	ANODE 1 ANODE 2 GATE	STYLE 5: PIN 1. 2., 4. 3.	
STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	MT 1	STYLE 8: PIN 1.	SOURCE	STYLE 9: PIN 1.	GATE	STYLE 10: PIN 1.	SOURCE

2., 4. GATE 3. DRAIN

DRAIN

2., 4. 3. DRAIN

2., 4. GATE 3. MT 2

DOCUMENT NUMBER:	98ASB42049B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-225		PAGE 1 OF 1	

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

2., 4. 3. GATE

ANODE

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales